



General Description

- Proprietary α MOS5™ technology
- Low $R_{DS(ON)}$
- Optimized switching parameters for better EMI performance
- Enhanced body diode for robustness and fast reverse recovery

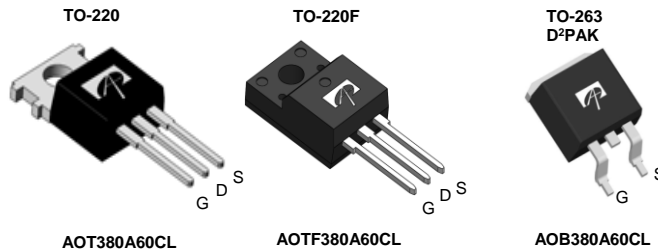
Applications

- SMPS with PFC, Flyback and LLC topologies
- Silver ATX ,adapter, TV, lighting, Server power

Product Summary

$V_{DS} @ T_{j,max}$	700V
I_{DM}	44A
$R_{DS(ON),max}$	< 0.38 Ω
$Q_{g,typ}$	18nC
$E_{oss} @ 400V$	2.6 μ J

100% UIS Tested
100% R_g Tested



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AOT380A60CL	TO-220	Tube	1000
AOTF380A60CL	TO-220F	Tube	1000
AOB380A60CL	TO263	Tape and reel	800

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	AOT(B)380A60CL	AOTF380A60CL	Units
Drain-Source Voltage	V_{DS}	600		V
Gate-Source Voltage	V_{GS}	± 20		V
Gate-Source Voltage (dynamic) AC($f > 1\text{Hz}$)	V_{GS}	± 30		V
Continuous Drain Current	$T_C=25^\circ\text{C}$	11	11*	A
	$T_C=100^\circ\text{C}$	7.2	7.2*	
Pulsed Drain Current ^C	I_{DM}	44		
Avalanche Current ^C	I_{AR}	2.5		A
Repetitive avalanche energy ^C	E_{AR}	3.1		mJ
Single pulsed avalanche energy ^G ($T_J=25^\circ\text{C}$, $V_{GS}=10\text{V}$, $I_L=2\text{Apk}$, $L=105\text{mH}$, $R_{GS}=25\Omega$)	E_{AS}	210		mJ
MOSFET dv/dt ruggedness	dv/dt	100		V/ns
Peak diode recovery dv/dt		20		
Power Dissipation ^B	$T_C=25^\circ\text{C}$	131	27	W
	Derate above 25°C	1.0	0.2	W/ $^\circ\text{C}$
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150		$^\circ\text{C}$
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	T_L	300		$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	AOT(B)380A60CL	AOTF380A60CL	Units
Maximum Junction-to-Ambient ^{A,D}	$R_{\theta JA}$	65	65	$^\circ\text{C/W}$
Maximum Case-to-sink ^A	$R_{\theta CS}$	0.5	--	$^\circ\text{C/W}$
Maximum Junction-to-Case	$R_{\theta JC}$	0.95	4.6	$^\circ\text{C/W}$

* Drain current limited by maximum junction temperature.

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V, T _J =25°C	600			V
		I _D =250μA, V _{GS} =0V, T _J =150°C		700		
BV _{DSS} /ΔT _J	Breakdown Voltage Temperature Coefficient	I _D =250μA, V _{GS} =0V		0.44		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =600V, V _{GS} =0V			1	μA
		V _{DS} =480V, T _J =125°C			10	
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =5V, I _D =250μA	2.6	3.2	3.8	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =5.5A		0.33	0.38	Ω
g _{FS}	Forward Transconductance	V _{DS} =10V, I _D =5.5A		9.3		S
V _{SD}	Diode Forward Voltage	I _S =5.5A, V _{GS} =0V		0.85	1.2	V
I _S	Maximum Body-Diode Continuous Current				11	A
I _{SM}	Maximum Body-Diode Pulsed Current ^C				44	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =100V, f=1MHz		955		pF
C _{oss}	Output Capacitance			29		pF
C _{o(er)}	Effective output capacitance, energy related ^H	V _{GS} =0V, V _{DS} =0 to 480V, f=1MHz		30		pF
C _{o(tr)}	Effective output capacitance, time related ^I			122		pF
C _{rss}	Reverse Transfer Capacitance	V _{GS} =0V, V _{DS} =100V, f=1MHz		2.4		pF
R _g	Gate resistance	f=1MHz		4.8		Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =480V, I _D =5.5A		18		nC
Q _{gs}	Gate Source Charge			7		nC
Q _{gd}	Gate Drain Charge			4.5		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =400V, I _D =5.5A, R _G =5Ω		20		ns
t _r	Turn-On Rise Time			13		ns
t _{D(off)}	Turn-Off DelayTime			43		ns
t _f	Turn-Off Fall Time			16		ns
t _{rr}	Body Diode Reverse Recovery Time			251		ns
I _{rm}	Peak Reverse Recovery Current	I _F =5.5A, di/dt=100A/μs, V _{DS} =400V		19		A
Q _{rr}	Body Diode Reverse Recovery Charge			3.1		μC

A. The value of R_{θJA} is measured with the device in a still air environment with T_A=25° C.

B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150° C. Ratings are based on low frequency and duty cycles to keep initial T_J=25° C.

D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.

G. This is the absolute maximum rating. Parts are 100% tested at T_J=25° C, L=60mH, I_{AS}=1A, V_{DD}=150V, R_G=25Ω.

H. C_{o(er)} is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{(BR)DSS}.

I. C_{o(tr)} is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{(BR)DSS}.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

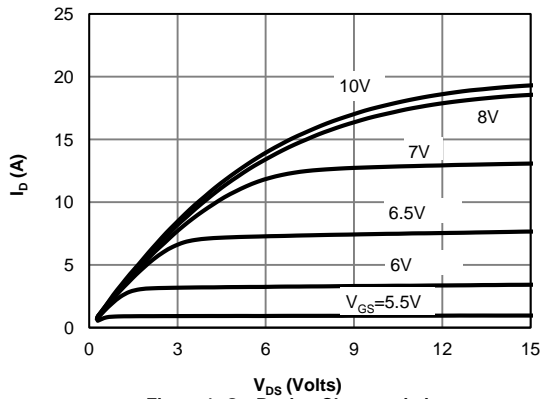


Figure 1: On-Region Characteristics

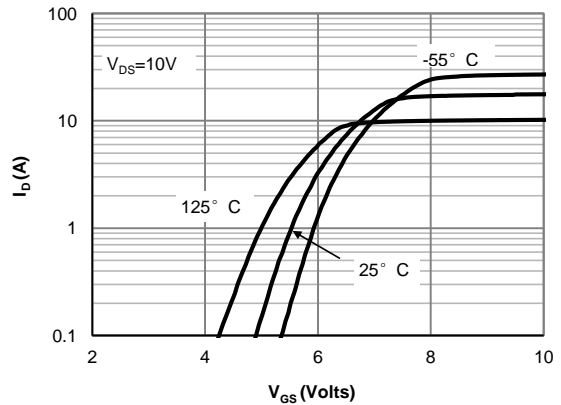


Figure 2: Transfer Characteristics

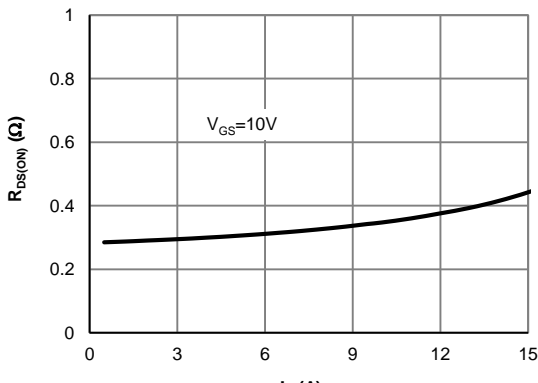


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

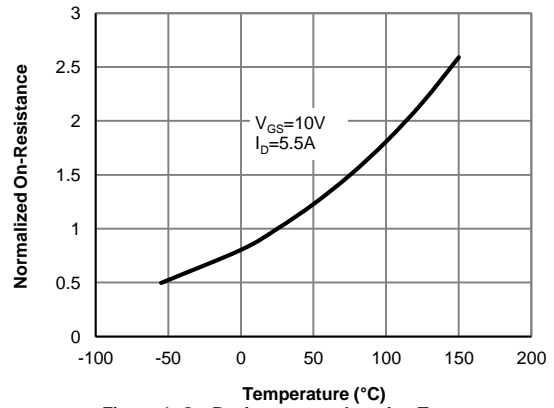


Figure 4: On-Resistance vs. Junction Temperature

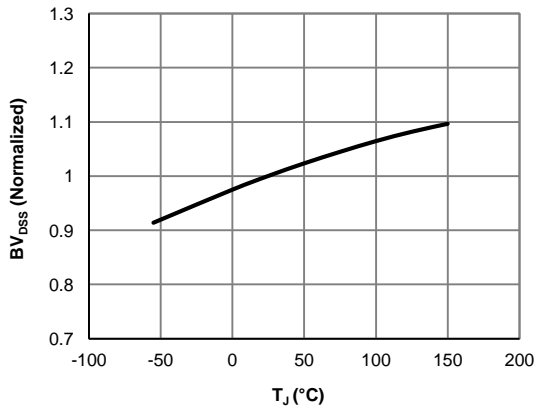


Figure 5: Break Down vs. Junction Temperature

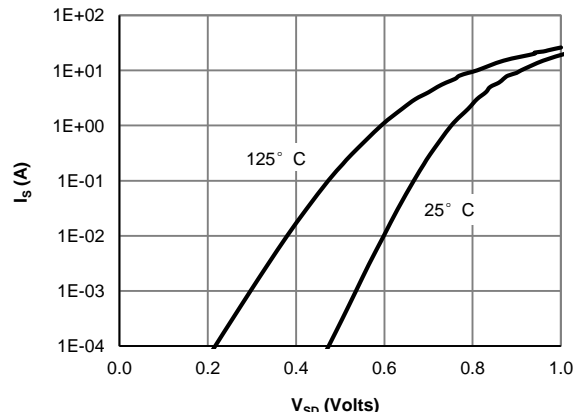


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

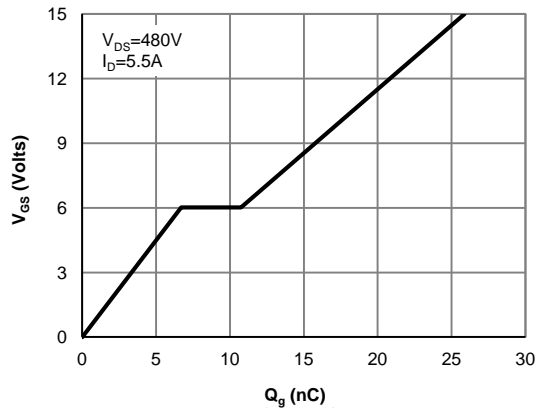


Figure 7: Gate-Charge Characteristics

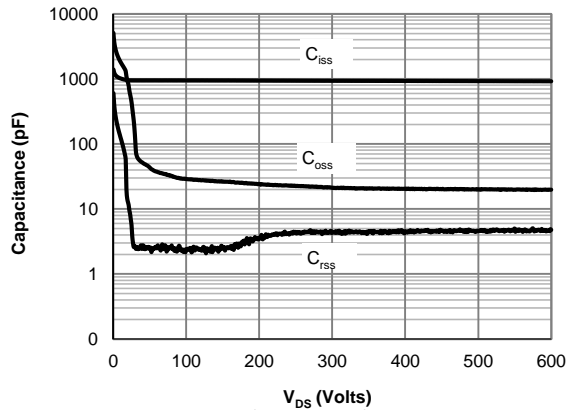


Figure 8: Capacitance Characteristics

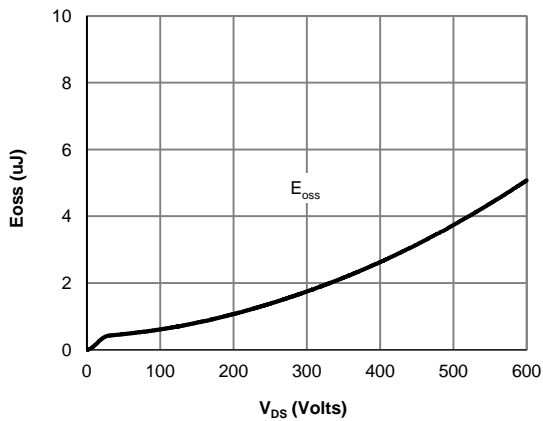


Figure 9: Coss stored Energy

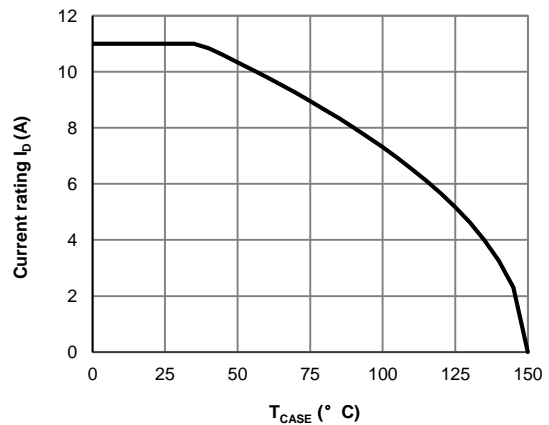


Figure 10: Current De-rating (Note F)

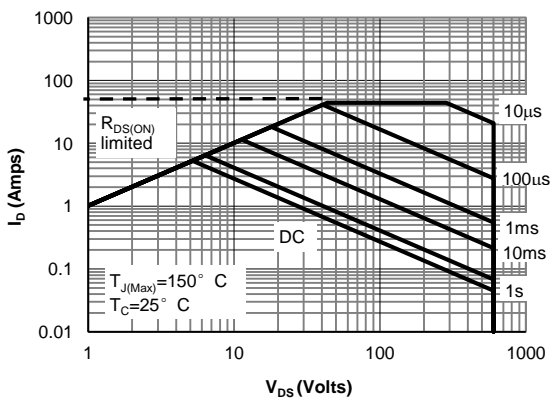


Figure 11: Maximum Forward Biased Safe Operating Area for AOTF380A60CL (Note F)

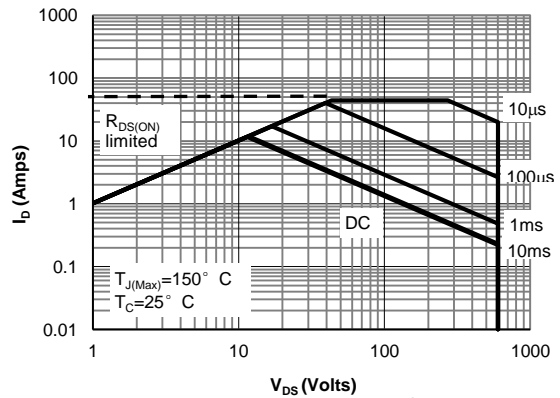


Figure 12: Maximum Forward Biased Safe Operating Area for AOT(B)380A60CL (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

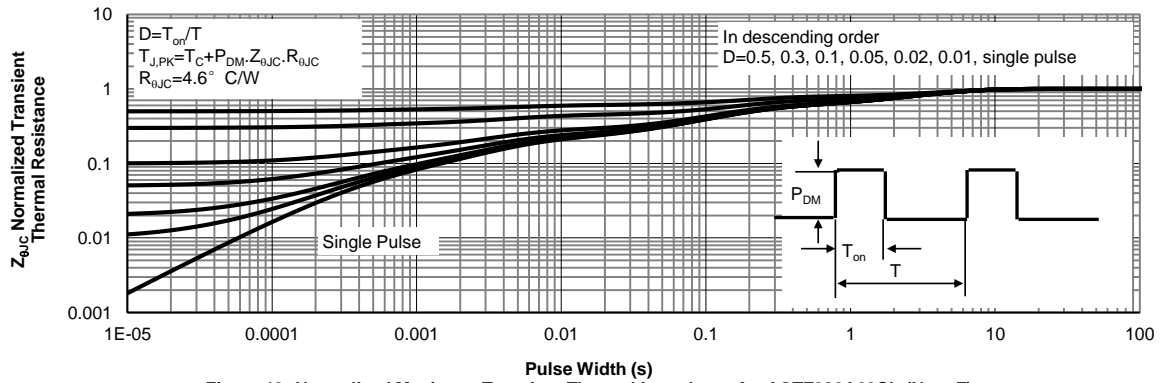


Figure 13: Normalized Maximum Transient Thermal Impedance for AOTF380A60CL (Note F)

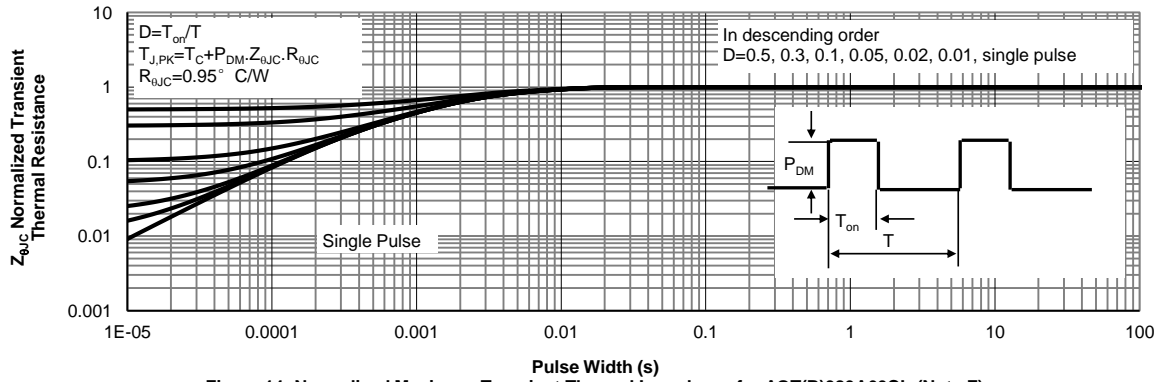
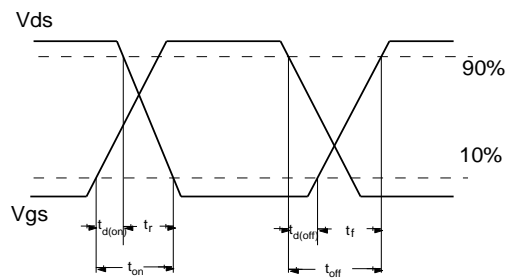


Figure 14: Normalized Maximum Transient Thermal Impedance for AOT(B)380A60CL (Note F)

Gate Charge Test Circuit & Waveform



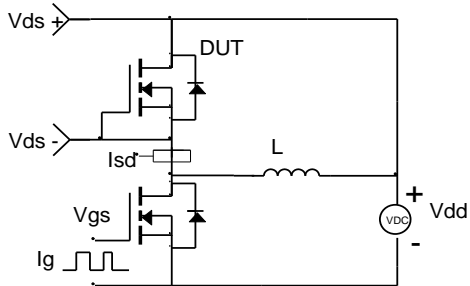
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



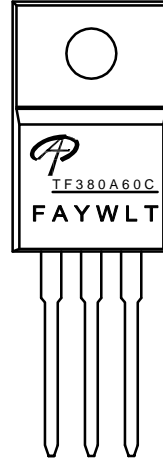
Diode Recovery Test Circuit & Waveforms





Document No.	PD-03161
Version	A
Title	AOTF380A60CL Marking Description

TO220F PACKAGE MARKING DESCRIPTION



Green product

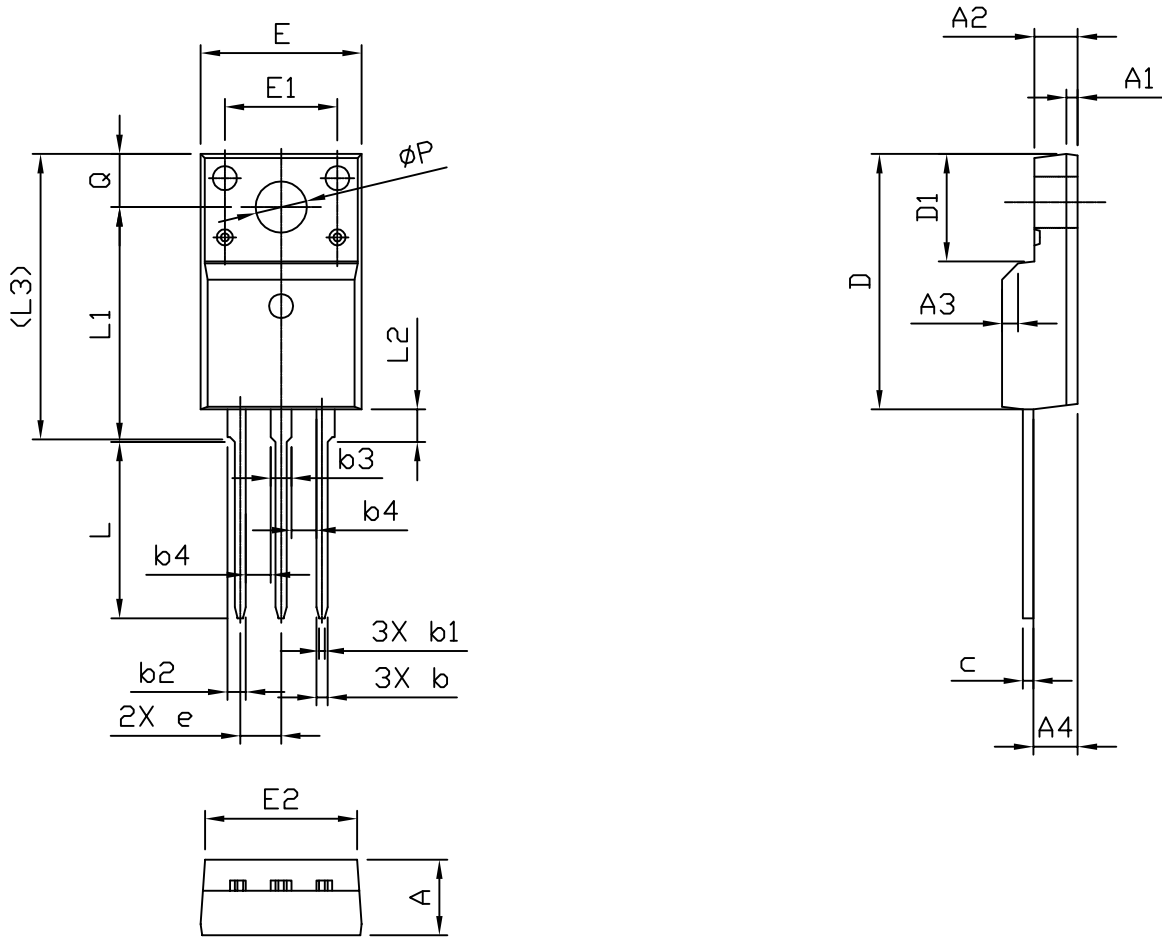
NOTE:

- LOGO - AOS Logo
- TF380A60C - Part number code
- F - Fab code
- A - Assembly location code
- Y - Year code
- W - Week code
- L&T - Assembly lot code

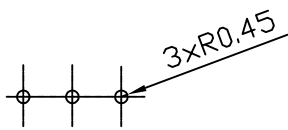
PART NO.	DESCRIPTION	CODE
AOTF380A60CL	Green product	<u>TF380A60C</u>



TO220F PACKAGE OUTLINE



RECOMMENDATION OF HOLE PATTERN



UNIT: mm

SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.50	4.70	4.90	0.177	0.185	0.193
A1	---	0.70	---	---	0.028	---
A2	2.34	2.54	2.74	0.092	0.100	0.108
A3	1X45°			0.039X45°		
A4	2.66	2.76	2.86	0.105	0.106	0.113
b	0.59	0.69	0.79	0.023	0.027	0.031
b1	0.25	0.35	0.45	0.010	0.014	0.018
b2	1.14	1.24	1.29	0.045	0.049	0.051
b3	1.28	1.38	1.43	0.050	0.054	0.056
b4	1.40 MIN.			0.055 MIN.		
c	0.59	0.64	0.74	0.023	0.025	0.029
D	15.67	15.87	16.07	0.617	0.625	0.633
D1	6.48	6.68	6.88	0.255	0.263	0.271
e	2.54 BSC			0.100 BSC.		
E	9.96	10.16	10.36	0.392	0.400	0.408
E1	---	7.00	---	---	0.276	---
E2	9.26	9.46	9.66	0.365	0.372	0.380
L	10.76	10.96	11.16	0.424	0.431	0.439
L1	14.39	14.59	14.79	0.567	0.574	0.582
L2	1.70	2.03	2.20	0.067	0.080	0.087
(L3)	---	17.75	17.90	---	0.699	0.705
Q	3.20	3.30	3.40	0.126	0.130	0.134
øP	3.08	3.18	3.28	0.121	0.125	0.129

NOTE

1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS. MOLD FLASH SHOULD BE LESS THAN 6 MIL.
2. TOLERANCE 0.100 MILLIMETERS UNLESS OTHERWISE SPECIFIED.
3. CONTROLLING DIMENSION IS MILLIMETER.
CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.
4. DIMENSION WITH "()" IS FOR REFERENCE.



AOS Semiconductor Product Reliability Report

AOTF380A60CL, rev A

Plastic Encapsulated Device

ALPHA & OMEGA Semiconductor, Inc

www.aosmd.com

Apr, 2019

This AOS product reliability report summarizes the qualification result for AOTF380A60CL. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AOTF380A60CL passes AOS quality and reliability requirements. The released product will be categorized by the process family and be routine monitored for continuously improving the product quality.

I. Reliability Stress Test Summary and Results

Test Item	Test Condition	Time Point	Total Sample Size	Number of Failures	Reference Standard
HTGB	Temp = 150°C , Vgs=100% of Vgsmax	168 / 500 / 1000 hours	462 pcs	0	JESD22-A108
HTRB	Temp = 150°C , Vds=100% of Vdsmax	168 / 500 / 1000 hours	462 pcs	0	JESD22-A108
HAST	130°C , 85%RH, 33.3 psia, Vds = 80% of Vdsmax up to 42V	96 hours	693 pcs	0	JESD22-A110
H3TRB	85°C , 85%RH, Vds = 80% of Vdsmax up to 100V	1000 hours	693 pcs	0	JESD22-A101
Autoclave	121°C , 29.7psia, RH=100%	96 hours	924 pcs	0	JESD22-A102
Temperature Cycle	-65°C to 150°C , air to air,	1000cycles	924 pcs	0	JESD22-A104
HTSL	Temp = 150°C	1000 hours	693 pcs	0	JESD22-A103
IOL	Δ Tj = 100°C	8572 cycles	693 pcs	0	MIL-STD-750 Method 1037
Resistance to Solder Heat	Temp = 270°C	15 seconds	30 pcs	0	JESD22-B106

Note: The reliability data presents total of available generic data up to the published date.

II. Reliability Evaluation

FIT rate (per billion): 3.82

MTTF = 29919 years

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size. Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

Failure Rate = $\text{Chi}^2 \times 10^9 / [2 (N) (H) (Af)] = 3.82$

MTTF = $10^9 / \text{FIT} = 29919$ years

Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval

N = Total Number of units from burn-in tests

H = Duration of burn-in testing

Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C)

Acceleration Factor [**Af**] = $\text{Exp} [Ea / k (1/Tj u - 1/Tj s)]$

Acceleration Factor ratio list:

	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af	259	87	32	13	5.64	2.59	1

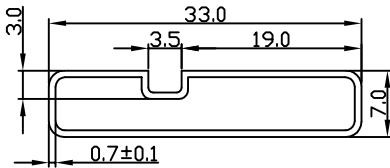
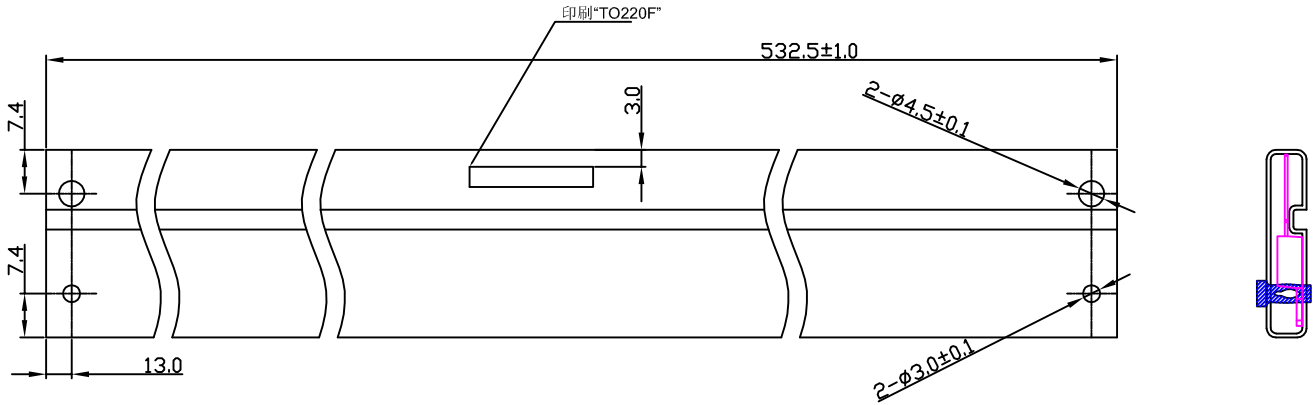
Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16

Tj u = The use junction temperature in degree (Kelvin), K = C+273.16

k = Boltzmann's constant, $8.617164 \times 10^{-5} \text{eV} / \text{K}$



TO220F/TO220FL TUBE



2:1

NOTE

1. TUBE

- MATERIAL : POLYVINYL CHLORIDE
- COLOR : TRANSPARENCY
- PRINT COLOR: BLACK
- CAMBAR : 1.5 MAX
- ALL DIMENSION: MM

2. PIN

- COLOR : GREEN (ONE PIN MUST BE INSERTED IN LEFT-SIDE OF " TO220F" AND ANOTHER PIN IS FREE.)

3. ALL UNSPECIFICATED SPECIFICATIONS FOLLOW TUBE GENERAL SPEC. UNSPECIFICATED TOLERANCE ± 0.2

4. PACKING Q'TY :

PKG	Q'TY(PCS)
TO220F/ TO220FL	50